# Hiroyuki Nishinaka

## List of Publications by Year in descending order

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|---|---|---|---|
| 48<br>papers | 1,741<br>citations | 331670<br>21<br>h-index | 276875<br>41<br>g-index |
| 48<br>all docs | 48<br>docs citations | 48<br>times ranked | 1513<br>citing authors |

| # | ARTICLE | IF | CITATIONS |
|---|---|---|---|
| 1 | Plan-view TEM observation of a single-domain Îº-Ga<sub>2</sub>O<sub>3</sub> thin film grown on Îµ-GaFeO<sub>3</sub> substrate using GaCl<sub>3</sub> precursor by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2022, 61, 018002. | 1.5 | 14 |
| 2 | Observing the microstructure of a (001) Îº-Ga<sub>2</sub>O<sub>3</sub> thin film grown on a (âˆ’201) Î²-Ga<sub>2</sub>O<sub>3</sub> substrate using automated crystal orientation mapping transmission electron microscopy. CrystEngComm, 2022, 24, 3239-3245. | 2.6 | 5 |
| 3 | Alloying In<sub>2</sub>O<sub>3</sub>and Ga<sub>2</sub>O<sub>3</sub>on AlN templates for deep-ultraviolet transparent conductive films by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2022, 61, SC1037. | 1.5 | 6 |
| 4 | Investigation of deep level defects in n-type GaAsBi. , 2022, , . |  | 0 |
| 5 | Improving the photovoltaic properties of GaAs/GaAsBi pin diodes by inserting a compositionally graded layer at the hetero-interface. Semiconductor Science and Technology, 2022, 37, 065016. | 2.0 | 6 |
| 6 | Epitaxial growth of metastable c-plane rhombohedral indium tin oxide using mist chemical vapor deposition. Materials Science in Semiconductor Processing, 2022, 147, 106689. | 4.0 | 4 |
| 7 | Growth of indium-incorporated Îº-Ga2O3 thin film lattice-matched to the Îµ-GaFeO3 substrate. Materials Letters: X, 2022, 14, 100149. | 0.7 | 4 |
| 8 | Thermodynamically metastable <b>Î±</b>-, <b>Îµ</b>- (or <b>Îº</b>-), and <b>Î³</b>-Ga2O3: From material growth to device applications. APL Materials, 2022, 10, . | 5.1 | 23 |
| 9 | Epitaxial growth of Î³-(AlxGa1-x)2O3 alloy thin films on spinel substrates via mist chemical vapor deposition. Journal of Alloys and Compounds, 2021, 851, 156927. | 5.5 | 14 |
| 10 | Rapid homoepitaxial growth of (010) Î²-Ga2O3 thin films via mist chemical vapor deposition. Materials Science in Semiconductor Processing, 2021, 128, 105732. | 4.0 | 35 |
| 11 | Deep levels and carrier capture kinetics in n-GaAsBi alloys investigated by deep level transient spectroscopy. Journal Physics D: Applied Physics, 2021, 54, 345109. | 2.8 | 11 |
| 12 | Fabrication of a GaAs/GaNAsBi solar cell and its performance improvement by thermal annealing. Semiconductor Science and Technology, 2021, 36, 095020. | 2.0 | 7 |
| 13 | Growth of Metastable Î±-Ga&lt;sub&gt;2&lt;/sub&gt;O&lt;sub&gt;3&lt;/sub&gt; Epitaxial Thin Film on Flexible Synthetic Mica by Insertion Î±-Fe&lt;sub&gt;2&lt;/sub&gt;O&lt;sub&gt;3&lt;/sub&gt; Buffer Layer. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 738-744. | 0.2 | 2 |
| 14 | Phase control of Î±- and Îº-Ga2O3 epitaxial growth on LiNbO3 and LiTaO3 substrates using Î±-Fe2O3 buffer layers. AIP Advances, 2020, 10, . | 1.3 | 18 |
| 15 | Determination of Zn-containing sites in<i>Î²</i>-Ga<sub>2</sub>O<sub>3</sub>film grown through mist chemical vapor deposition via X-ray absorption spectroscopy. Japanese Journal of Applied Physics, 2020, 59, 070909. | 1.5 | 4 |
| 16 | van der Waals epitaxy of ferroelectric <i>Îµ</i>-gallium oxide thin film on flexible synthetic mica. Japanese Journal of Applied Physics, 2020, 59, 025503. | 1.5 | 15 |
| 17 | Epitaxial Growth of Bendable Cubic NiO and In2O3 Thin Films on Synthetic Mica for p- and n-type Wide-Bandgap Semiconductor Oxides. MRS Advances, 2020, 5, 1671-1679. | 0.9 | 9 |
| 18 | Single-Domain and Atomically Flat Surface of Îº-Ga<sub>2</sub>O<sub>3</sub> Thin Films on FZ-Grown Îµ-GaFeO<sub>3</sub> Substrates via Step-Flow Growth Mode. ACS Omega, 2020, 5, 29585-29592. | 3.5 | 24 |

| # | ARTICLE | IF | CITATIONS |
|---|---|---|---|
| 19 | A preliminary study on mist CVD-derived ferroelectric Hf<sub>1âˆ’<i>x</i> </sub>Zr<i> <sub>x</sub> </i>O<sub>2</sub> films featuring its possibility of suitable operation for non-volatile analog memory. Japanese Journal of Applied Physics, 2020, 59, SPPB09. | 1.5 | 5 |
| 20 | Mist Chemical Vapor Deposition 2. Springer Series in Materials Science, 2020, , 243-255. | 0.6 | 1 |
| 21 | Mist chemical vapor deposition study of 20 and 100 nm thick undoped ferroelectric hafnium oxide films on n+-Si(100) substrates. Japanese Journal of Applied Physics, 2019, 58, SLLB10. | 1.5 | 2 |
| 22 | Impact of a small change in growth temperature on the tail states of GaAsBi. Journal of Applied Physics, 2019, 126, 045702. | 2.5 | 14 |
| 23 | PEDOT:PSS/GaAs<sub>1âˆ’<i>x</i> </sub>Bi<i> <sub>x</sub> </i> organicâ€“inorganic solar cells. Japanese Journal of Applied Physics, 2019, 58, 060907. | 1.5 | 16 |
| 24 | Growth and characterization of F-doped Î±-Ga2O3 thin films with low electrical resistivity. Thin Solid Films, 2019, 682, 18-23. | 1.8 | 23 |
| 25 | Microstructures of $varepsilon - mathrm{Ga}_{2}mathrm{O}_{3}$ thin film on (100) TiO2 substrate by mist chemical vapor deposition. , 2019, , . |  | 0 |
| 26 | Heteroepitaxial growth of Îµ-(Al<i>x</i>Ga1âˆ’<i>x</i>)2O3 alloy films on <i>c</i>-plane AlN templates by mist chemical vapor deposition. Applied Physics Letters, 2018, 112, . | 3.3 | 59 |
| 27 | Incorporation of indium into Îµ-gallium oxide epitaxial thin films grown <i>via</i> mist chemical vapour deposition for bandgap engineering. CrystEngComm, 2018, 20, 1882-1888. | 2.6 | 54 |
| 28 | Microstructures and rotational domains in orthorhombic Îµ-Ga<sub>2</sub>O<sub>3</sub> thin films. Japanese Journal of Applied Physics, 2018, 57, 115601. | 1.5 | 61 |
| 29 | Heteroepitaxial growth of single-phase Îµ-Ga<sub>2</sub>O<sub>3</sub> thin films on <i>c</i>-plane sapphire by mist chemical vapor deposition using a NiO buffer layer. CrystEngComm, 2018, 20, 6236-6242. | 2.6 | 38 |
| 30 | Use of mist chemical vapor deposition to impart ferroelectric properties to Îµ-Ga2O3 thin films on SnO2/c-sapphire substrates. Materials Letters, 2018, 232, 47-50. | 2.6 | 26 |
| 31 | Mist Chemical Vapor Deposition of Single-Phase Metastable Rhombohedral Indium Tin Oxide Epitaxial Thin Films with High Electrical Conductivity and Transparency on Various Î±-Al<sub>2</sub>O<sub>3</sub> Substrates. Crystal Growth and Design, 2018, 18, 4022-4028. | 3.0 | 24 |
| 32 | Stoichiometric control for heteroepitaxial growth of smooth Îµ-Ga<sub>2</sub>O<sub>3</sub>thin films on<i>c</i>-plane AlN templates by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2017, 56, 078004. | 1.5 | 68 |
| 33 | Epitaxial growth of Î±-Ga2O3 thin films on a-, m-, and r-plane sapphire substrates by mist chemical vapor deposition using Î±-Fe2O3 buffer layers. Materials Letters, 2017, 205, 28-31. | 2.6 | 63 |
| 34 | Heteroepitaxial growth of Îµ-Ga&lt;inf&gt;2&lt;/inf&gt;O&lt;inf&gt;3&lt;/inf&gt; thin films on cubic (111) GGG substrates by mist chemical vapor deposition. , 2017, , . |  | 5 |
| 35 | Solution-based mist CVD technique for CH<sub>3</sub>NH<sub>3</sub>Pb(Br<sub>1âˆ’</sub>) Tj ETQq1 1 0.784314 rgBT /Overlock<br>Applied Physics, 2016, 55, 100308. | 1.5 | 21 |
| 36 | Heteroepitaxial growth of Îµ-Ga<sub>2</sub>O<sub>3</sub> thin films on cubic (111) MgO and (111) yttria-stablized zirconia substrates by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 1202BC. | 1.5 | 84 |

| # | Article | IF | Citations |
|---|---|---|---|
| 37 | Growth characteristics of singleâ€crystalline ZnMgO layers by ultrasonic spray assisted mist CVD technique. Physica Status Solidi (B): Basic Research, 2010, 247, 1460-1463. | 1.5 | 37 |
| 38 | Mist Deposition Technique as a Green Chemical Route for Synthesizing Oxide and Organic Thin Films. Materials Research Society Symposia Proceedings, 2009, 1220, 4061. | 0.1 | 3 |
| 39 | Junction properties of nitrogenâ€doped ZnO thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3088-3090. | 0.8 | 8 |
| 40 | Step-flow growth of homoepitaxial ZnO thin films by ultrasonic spray-assisted MOVPE. Journal of Crystal Growth, 2008, 310, 5007-5010. | 1.5 | 23 |
| 41 | Growth of Crystalline Zinc Oxide Thin Films by Fine-Channel-Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 4669. | 1.5 | 109 |
| 42 | Ultrasonic spray assisted Mist-CVD method for high-quality crystalline and amorphous oxide semiconductors growth. Materials Research Society Symposia Proceedings, 2008, 1113, 1. | 0.1 | 0 |
| 43 | Low-Temperature Growth of ZnO Thin Films by Linear Source Ultrasonic Spray Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2007, 46, 6811-6813. | 1.5 | 65 |
| 44 | Carrier concentration dependence of band gap shift in n-type ZnO:Al films. Journal of Applied Physics, 2007, 101, 083705. | 2.5 | 380 |
| 45 | Zno-based thin films synthesized by atmospheric pressure mist chemical vapor deposition. Journal of Crystal Growth, 2007, 299, 1-10. | 1.5 | 160 |
| 46 | Linear-Source Ultrasonic Spray Chemical Vapor Deposition Method for Fabrication of ZnMgO Films and Ultraviolet Photodetectors. Japanese Journal of Applied Physics, 2006, 45, L857-L859. | 1.5 | 87 |
| 47 | Fabrication OF ZnO and ZnMgO Thin Films and UV Photodetectors by Mist Chemical Vapor Deposition Method. Materials Research Society Symposia Proceedings, 2006, 957, 1. | 0.1 | 1 |
| 48 | Carrier concentration induced band-gap shift in Al-doped Zn1âˆ’xMgxO thin films. Applied Physics Letters, 2006, 89, 262107. | 3.3 | 103 |